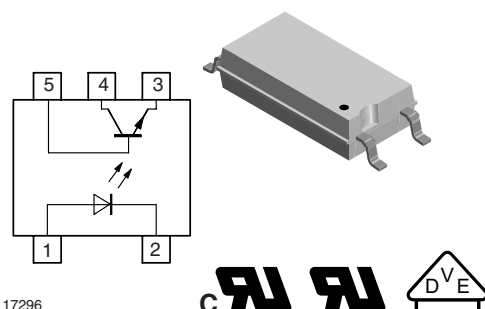


Optocoupler, Phototransistor Output, SOP-6L5, 110 °C Rated, Half Pitch, Long Mini-Flat Package



17296

FEATURES

- SMD low profile 5 pin package
- Isolation test voltage 5000 V_{RMS}
- CTR flexibility available see order information
- Special construction
- Extra low coupling capacitance
- Connected base
- DC input with transistor output
- Temperature range - 40 °C to 110 °C
- Thickness through insulation ≥ 0.75 mm
- Creepage distance > 8 mm
- Lead (Pb)-free component
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC



RoHS
COMPLIANT

DESCRIPTION

The TCLT1110 series consists of a phototransistor optically coupled to a gallium arsenide infrared-emitting diode in a 5-lead SOP-6L package.

The elements are mounted on one leadframe providing a fixed distance between input and output for highest safety requirements.

AGENCY APPROVALS

- UL1577, file no. E76222 system code W, double protection
- CUL - file no. E52744, equivalent to CSA 22.2 bulletin 5A
- DIN EN 60747-5-2 (VDE 0884)

APPLICATIONS

- Switchmode power supplies
- Computer peripheral interface
- Microprocessor system interface

ORDER INFORMATION	
PART	REMARKS
TCLT1110	CTR 50 to 600 %, SOP-6L5
TCLT1111	CTR 40 to 80 %, SOP-6L5
TCLT1112	CTR 63 to 125 %, SOP-6L5
TCLT1113	CTR 100 to 200 %, SOP-6L5
TCLT1114	CTR 160 to 320 %, SOP-6L5
TCLT1115	CTR 50 to 150 %, SOP-6L5
TCLT1116	CTR 100 to 300 %, SOP-6L5
TCLT1117	CTR 80 to 160 %, SOP-6L5
TCLT1118	CTR 130 to 260 %, SOP-6L5
TCLT1119	CTR 200 to 400 %, SOP-6L5

Note

Available only on tape and reel.

ABSOLUTE MAXIMUM RATINGS ⁽¹⁾				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
INPUT				
Reverse voltage		V_R	6	V
Forward current		I_F	60	mA
Forward surge current	$t_p \leq 10 \mu s$	I_{FSM}	1.5	A
Power dissipation		P_{diss}	100	mW
Junction temperature		T_j	125	°C
OUTPUT				
Collector emitter voltage		V_{CEO}	70	V
Emitter collector voltage		V_{ECO}	7	V
Collector current		I_C	50	mA
Collector peak current	$t_p/T = 0.5, t_p \leq 10 ms$	I_{CM}	100	mA
Power dissipation		P_{diss}	150	mW
Junction temperature		T_j	125	°C
COUPLER				
Isolation test voltage (RMS)		V_{ISO}	5000	V_{RMS}
Total power dissipation		P_{tot}	250	mW
Operating ambient temperature range		T_{amb}	- 40 to + 110	°C
Storage temperature range		T_{stg}	- 40 to + 110	°C
Soldering temperature ⁽²⁾		T_{sld}	260	°C

Notes

⁽¹⁾ $T_{amb} = 25 \text{ °C}$, unless otherwise specified.

Stresses in excess of the absolute Maximum Ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute Maximum Rating for extended periods of the time can adversely affect reliability.

⁽²⁾ Refer to reflow profile for soldering conditions for surface mounted devices.

ELECTRICAL CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
INPUT						
Forward voltage	$I_F = 50 \text{ mA}$	V_F		1.25	1.6	V
Junction capacitance	$V_R = 0 \text{ V}, f = 1 \text{ MHz}$	C_j		50		pF
OUTPUT						
Collector emitter voltage	$I_C = 1 \text{ mA}$	V_{CEO}	70			V
Emitter collector voltage	$I_E = 100 \mu A$	V_{ECO}	7			V
Collector emitter cut-off current	$V_{CE} = 20 \text{ V}, I_F = 0 \text{ A}, E = 0$	I_{CEO}		10	100	nA
COUPLER						
Collector emitter saturation voltage	$I_F = 10 \text{ mA}, I_C = 1 \text{ mA}$	V_{CEsat}			0.3	V
Cut-off frequency	$V_{CE} = 5 \text{ V}, I_F = 10 \text{ mA}, R_L = 100 \Omega$	f_c		110		kHz
Coupling capacitance	$f = 1 \text{ MHz}$	C_k		0.3		pF

Note

$T_{amb} = 25 \text{ °C}$, unless otherwise specified.

Minimum and maximum values are testing requirements. Typical values are characteristics of the device and are the result of engineering evaluation. Typical values are for information only and are not part of the testing requirements.



Optocoupler, Phototransistor Output,
SOP-6L5, 110 °C Rated,
Half Pitch, Long Mini-Flat Package

Vishay Semiconductors

CURRENT TRANSFER RATIO

PARAMETER	TEST CONDITION	PART	SYMBOL	MIN.	TYP.	MAX.	UNIT
I_C/I_F	$V_{CE} = 5\text{ V}, I_F = 5\text{ mA}$	TCLT1110	CTR	50		600	%
	$V_{CE} = 5\text{ V}, I_F = 10\text{ mA}$	TCLT1111	CTR	40		80	%
		TCLT1112	CTR	63		125	%
		TCLT1113	CTR	100		200	%
		TCLT1114	CTR	160		320	%
	$V_{CE} = 5\text{ V}, I_F = 1\text{ mA}$	TCLT1111	CTR	13	30		%
		TCLT1112	CTR	22	45		%
		TCLT1113	CTR	34	70		%
		TCLT1114	CTR	56	100		%
	$V_{CE} = 5\text{ V}, I_F = 5\text{ mA}$	TCLT1115	CTR	50		150	%
		TCLT1116	CTR	100		300	%
		TCLT1117	CTR	80		160	%
		TCLT1118	CTR	130		260	%
		TCLT1119	CTR	200		400	%

MAXIMUM SAFETY RATINGS

PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
INPUT						
Forward current		I_F			130	mA
OUTPUT						
Power dissipation		P_{diss}			265	mW
COUPLER						
Rated impulse voltage		V_{IOTM}			8	kV
Safety temperature		T_{si}			150	°C

Note

According to DIN EN 60747-5-2 (VDE 0884)/DIN EN 60747-5-5 pending (see figure 1). This optocoupler is suitable for safe electrical isolation only within the safety ratings. Compliance with the safety ratings shall be ensured by means of suitable protective circuits.

INSULATION RATED PARAMETERS

PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Partial discharge test voltage - routine test	100 %, $t_{test} = 1\text{ s}$	V_{pd}	1.6			kV
Partial discharge test voltage - lot test (sample test)	$t_{Tr} = 60\text{ s}, t_{test} = 10\text{ s},$ (see figure 2)	V_{IOTM}	8			kV
		V_{pd}	1.3			kV
Insulation resistance	$V_{IO} = 500\text{ V}$	R_{IO}	10^{12}			Ω
	$V_{IO} = 500\text{ V}, T_{amb} = 100\text{ °C}$	R_{IO}	10^{11}			Ω
	$V_{IO} = 500\text{ V}, T_{amb} = 150\text{ °C}$ (construction test only)	R_{IO}	10^9			Ω

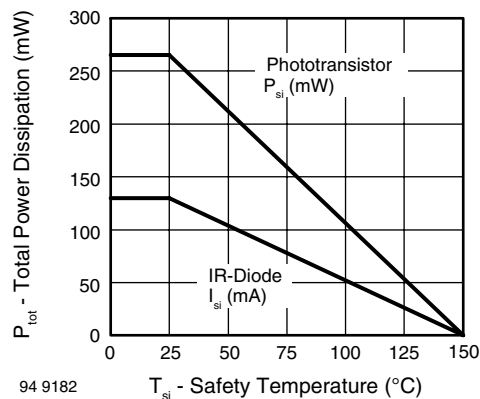


Fig. 1 - Derating Diagram

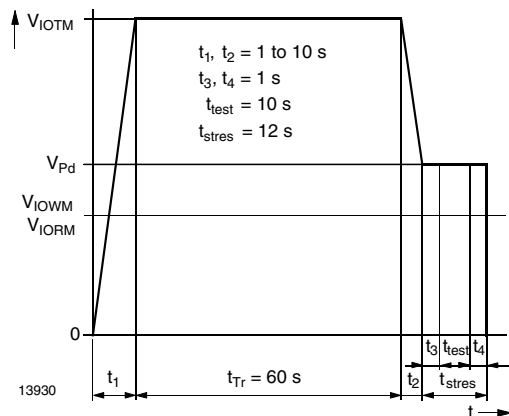


Fig. 2 - Test Pulse Diagram for Sample Test According to
DIN EN 60747-5-2 (VDE 0884)/DIN EN 60747-; IEC60747

SWITCHING CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Delay time	$V_S = 5\text{ V}$, $I_C = 2\text{ mA}$, $R_L = 100\ \Omega$, (see figure 3)	t_d		3.0		μs
Rise time	$V_S = 5\text{ V}$, $I_C = 2\text{ mA}$, $R_L = 100\ \Omega$, (see figure 3)	t_r		3.0		μs
Fall time	$V_S = 5\text{ V}$, $I_C = 2\text{ mA}$, $R_L = 100\ \Omega$, (see figure 3)	t_f		4.7		μs
Storage time	$V_S = 5\text{ V}$, $I_C = 2\text{ mA}$, $R_L = 100\ \Omega$, (see figure 3)	t_s		0.3		μs
Turn-on time	$V_S = 5\text{ V}$, $I_C = 2\text{ mA}$, $R_L = 100\ \Omega$, (see figure 3)	t_{on}		6.0		μs
Turn-off time	$V_S = 5\text{ V}$, $I_C = 2\text{ mA}$, $R_L = 100\ \Omega$, (see figure 3)	t_{off}		5.0		μs
Turn-on time	$V_S = 5\text{ V}$, $I_F = 10\text{ mA}$, $R_L = 1\text{ k}\Omega$, (see figure 4)	t_{on}		9.0		μs
Turn-off time	$V_S = 5\text{ V}$, $I_F = 10\text{ mA}$, $R_L = 1\text{ k}\Omega$, (see figure 4)	t_{off}		10.0		μs

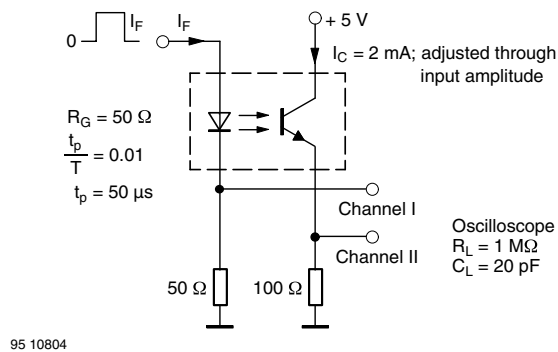


Fig. 3 - Test Circuit, Non-Saturated Operation

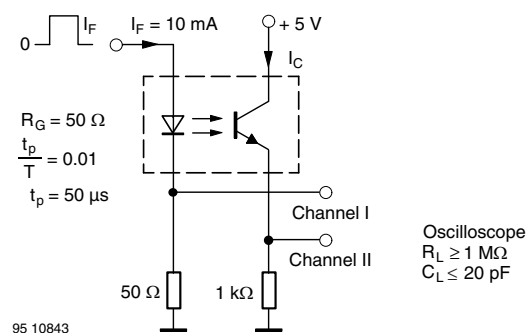


Fig. 4 - Test Circuit, Saturated Operation

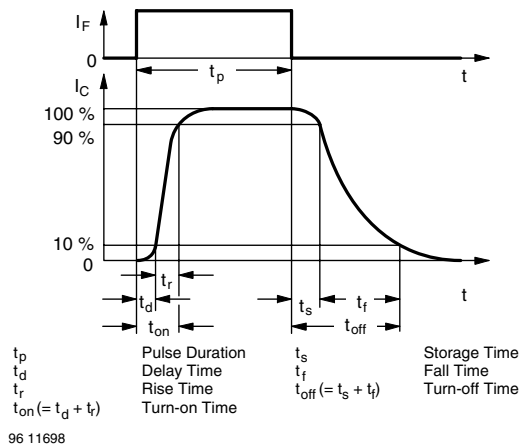


Fig. 5 - Switching Times

TYPICAL CHARACTERISTICS

$T_{amb} = 25\text{ °C}$, unless otherwise specified

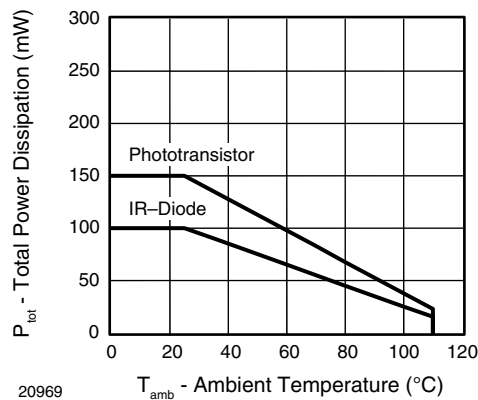


Fig. 6 - Total Power Dissipation vs. Ambient Temperature

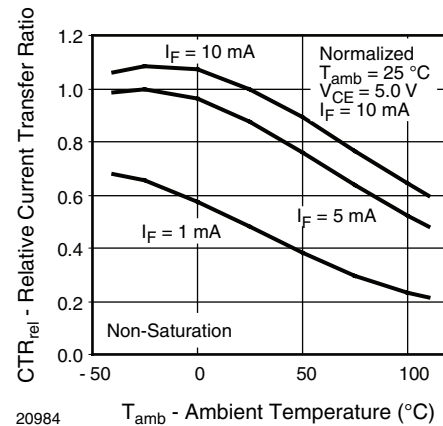


Fig. 8 - Relative Current Transfer Ratio vs. Ambient Temperature

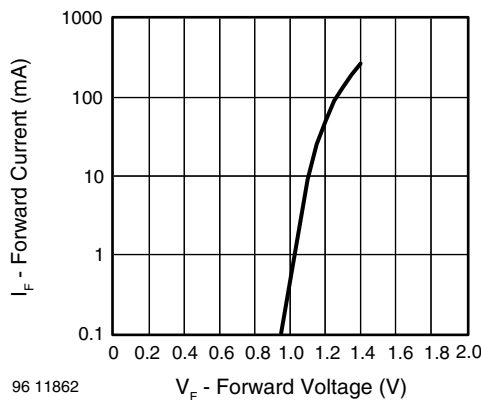


Fig. 7 - Forward Current vs. Forward Voltage

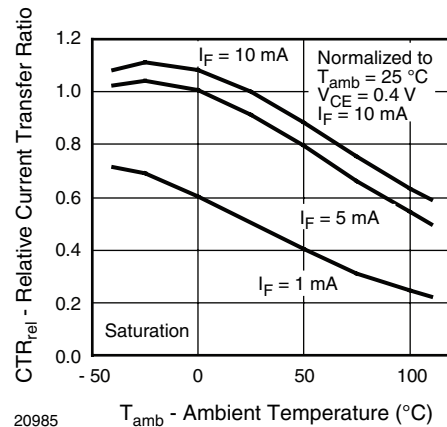


Fig. 9 - Relative Current Transfer Ratio vs. Ambient Temperature

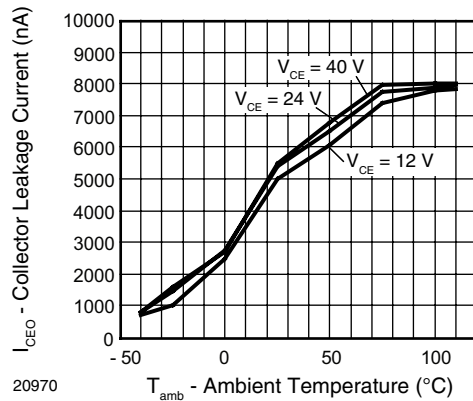


Fig. 10 - Collector Leakage Current vs. Ambient Temperature

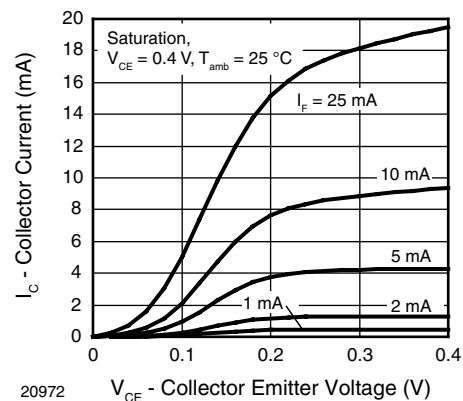


Fig. 13 - Collector Current vs. Collector Emitter Voltage

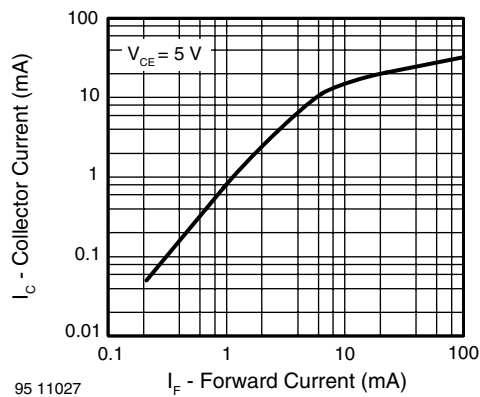


Fig. 11 - Collector Current vs. Forward Current

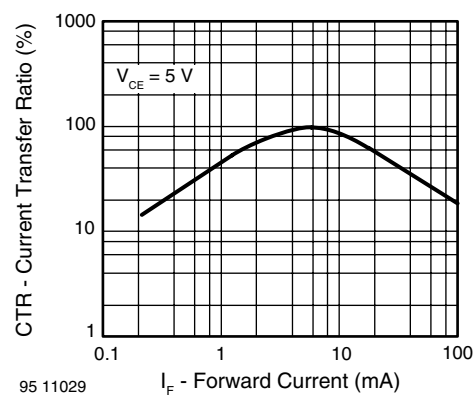


Fig. 14 - Current Transfer Ratio vs. Forward Current

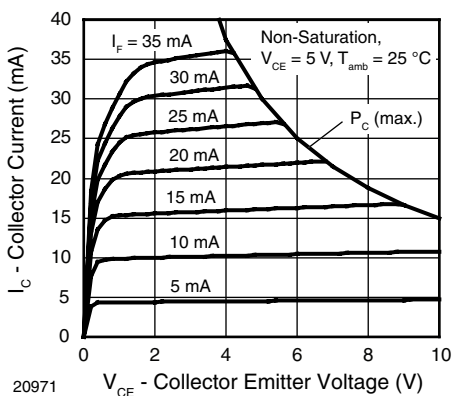


Fig. 12 - Collector Current vs. Collector Emitter Voltage

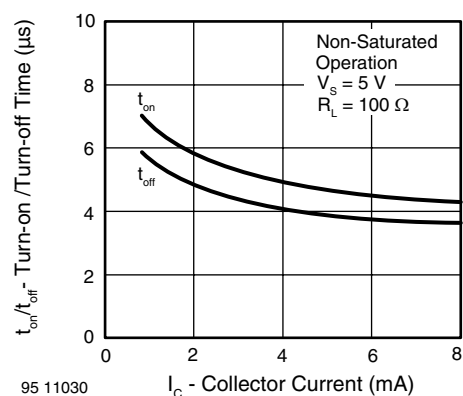


Fig. 15 - Turn-on/off Time vs. Collector Current

Optocoupler, Phototransistor Output,
SOP-6L5, 110 °C Rated,
Half Pitch, Long Mini-Flat Package

Vishay Semiconductors

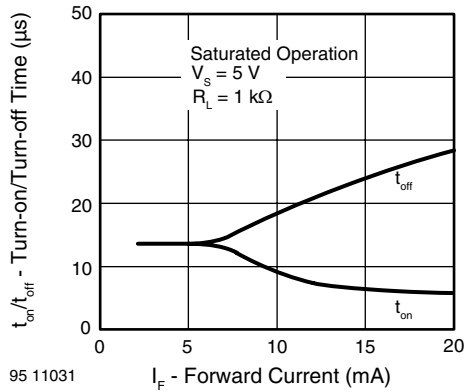
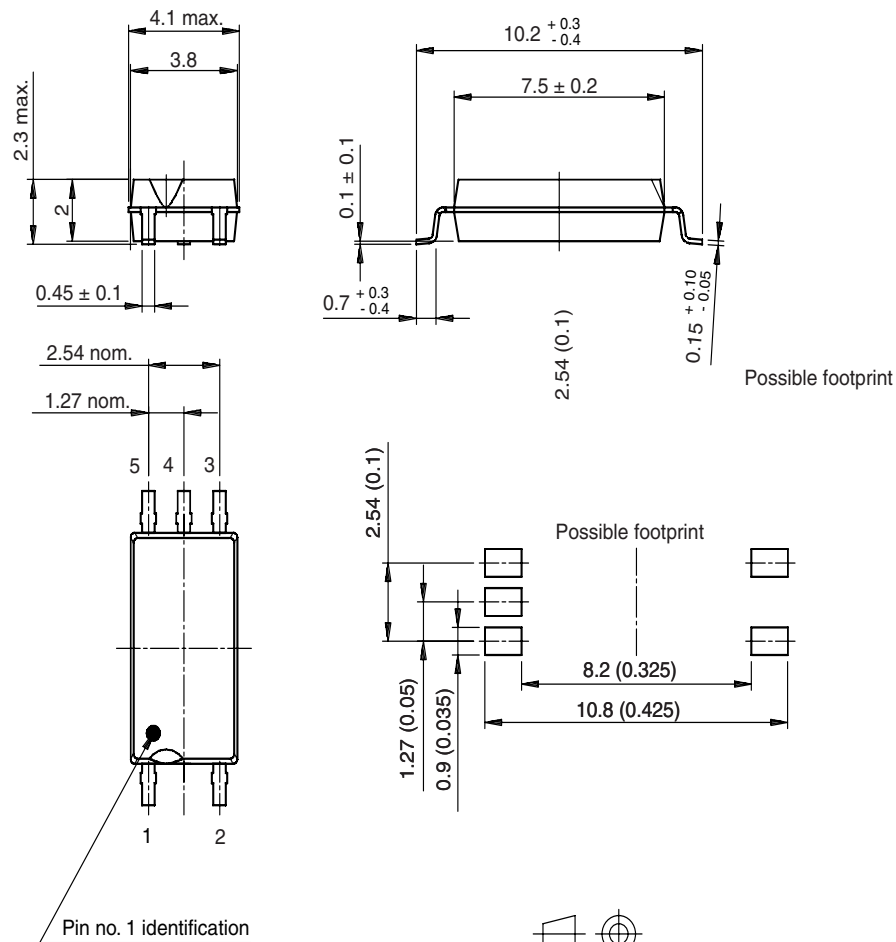


Fig. 16 - Turn-on/off Time vs. Forward Current

PACKAGE DIMENSIONS in millimeters (inches)



Drawing-No.: 6.544-5331.02-4
Issue: 2; 29.06.00

technical drawings
according to DIN
specifications

15227

Vishay Semiconductors Optocoupler, Phototransistor Output,
SOP-6L5, 110 °C Rated,
Half Pitch, Long Mini-Flat Package

OZONE DEPLETING SUBSTANCES POLICY STATEMENT

It is the policy of Vishay Semiconductor GmbH to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively.
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA.
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design
and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

Vishay Semiconductor GmbH, P.O.B. 3535, D-74025 Heilbronn, Germany



Notice

Specifications of the products displayed herein are subject to change without notice. Vishay Intertechnology, Inc., or anyone on its behalf, assumes no responsibility or liability for any errors or inaccuracies.

Information contained herein is intended to provide a product description only. No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document. Except as provided in Vishay's terms and conditions of sale for such products, Vishay assumes no liability whatsoever, and disclaims any express or implied warranty, relating to sale and/or use of Vishay products including liability or warranties relating to fitness for a particular purpose, merchantability, or infringement of any patent, copyright, or other intellectual property right.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Vishay for any damages resulting from such improper use or sale.